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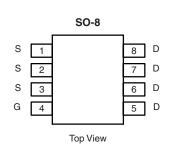
# N-Channel 150-V (D-S) MOSFET

PRODUCT SUMMARY					
V <sub>DS</sub> (V)	$R_{DS(on)}\left(\Omega\right)$	I <sub>D</sub> (A)			
150	0.050 at V <sub>GS</sub> = 10 V	5.0			

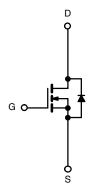
## **FEATURES**

- Halogen-free According to IEC 61249-2-21 Definition
- TrenchFET® Power MOSFETs
- Compliant to RoHS Directive 2002/95/EC





Ordering Information: Si4488DY-T1-E3 (Lead (Pb)-free) Si4488DY-T1-GE3 (Lead (Pb)-free and Halogen-free)



N-Channel MOSFET

Parameter	Symbol	10 s	Steady State	Unit	
Drain-Source Voltage		$V_{DS}$	150		V
Gate-Source Voltage		V <sub>GS</sub>	± 20		V
Continuous Drain Current /T 150 °C\8	T <sub>A</sub> = 25 °C	1_	5.0	3.5	
Continuous Drain Current (T <sub>J</sub> = 150 °C) <sup>a</sup>	T <sub>A</sub> = 70 °C	I <sub>D</sub>	4.0	2.8	
Pulsed Drain Current		I <sub>DM</sub>	50		Α
Avalanche Current	L = 0.1 mH	I <sub>AS</sub>	25		
Continuous Source Current (Diode Conduction) <sup>a</sup>	I <sub>S</sub>	2.8	1.4		
Manipus Barra Birata atian	T <sub>A</sub> = 25 °C	P <sub>D</sub>	3.1	1.56	W
Maximum Power Dissipation <sup>a</sup>	T <sub>A</sub> = 70 °C	] ' b	2.0	1.0	
Operating Junction and Storage Temperature Rar	T <sub>J</sub> , T <sub>stg</sub>	- 55 to 150		°C	

THERMAL RESISTANCE RATINGS						
Parameter	Symbol	Typical	Maximum	Unit		
Manifestor Location to Australia	t ≤ 10 s	R <sub>thJA</sub>	33	40		
Maximum Junction-to-Ambient <sup>a</sup>	Steady State	' ¹thJA	65	80	°C/W	
Maximum Junction-to-Foot (Drain)	Steady State	$R_{thJF}$	17	21		

a. Surface Mounted on 1" x 1" FR4 board.

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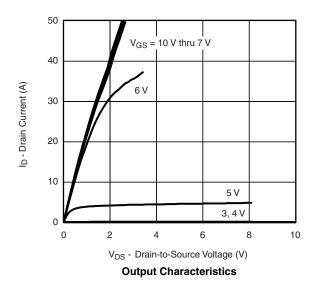
<b>SPECIFICATIONS</b> $T_J = 25$ °C	C, unless	otherwise noted				
Parameter	Symbol	Test Conditions Min.		Тур.	Max.	Unit
Static						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	2.0			V
Gate-Body Leakage	I <sub>GSS</sub>	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$			± 100	nA
Zara Cata Valtaria Duain Comment		V <sub>DS</sub> = 120 V, V <sub>GS</sub> = 0 V	1		4	
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> = 120 V, V <sub>GS</sub> = 0 V, T <sub>J</sub> = 55 °C			5	μΑ
On-State Drain Current <sup>a</sup>	I <sub>D(on)</sub>	$V_{DS} \ge 5 \text{ V}, V_{GS} = 10 \text{ V}$	50			Α
Drain-Source On-State Resistance <sup>a</sup> R <sub>DS</sub>		V <sub>GS</sub> = 10 V, I <sub>D</sub> = 5 A		0.041	0.050	Ω
Forward Transconductance <sup>a</sup>	9 <sub>fs</sub>	V <sub>DS</sub> = 15 V, I <sub>D</sub> = 5 A		18		S
Diode Forward Voltage <sup>a</sup>	$V_{SD}$	I <sub>S</sub> = 2.8 A, V <sub>GS</sub> = 0 V		0.75	1.1	V
Dynamic <sup>b</sup>						
Total Gate Charge	$Q_g$			30	36	
Gate-Source Charge	Q <sub>gs</sub>	$V_{DS} = 75 \text{ V}, V_{GS} = 10 \text{ V}, I_{D} = 5 \text{ A}$		8.5		nC
Gate-Drain Charge	$Q_{gd}$			8.5		
Gate Resistance	$R_{g}$		0.2	0.85	1.2	Ω
Turn-On Delay Time	t <sub>d(on)</sub>			12	18	
Rise Time	t <sub>r</sub>	$V_{DD}$ = 75 V, $R_L$ = 15 $\Omega$		7	11	
Turn-Off Delay Time	t <sub>d(off)</sub>	$I_D \cong 5 \text{ A}, V_{GEN} = 10 \text{ V}, R_g = 6 \Omega$		22	33	ns
Fall Time	t <sub>f</sub>			10	15	
Source-Drain Reverse Recovery Time	t <sub>rr</sub>	I <sub>F</sub> = 2.8 A, dI/dt = 100 A/μs		40	70	

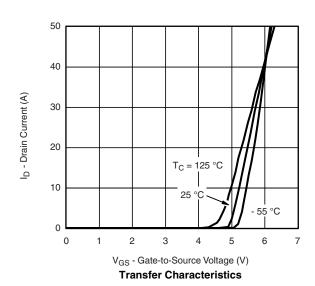
### Notes:

- a. Pulse test; pulse width  $\leq$  300  $\mu$ s, duty cycle  $\leq$  2 %. b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

# TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



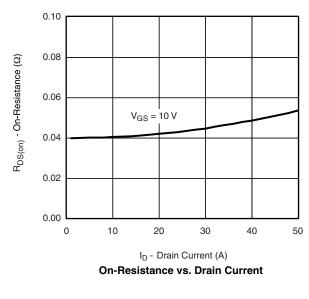


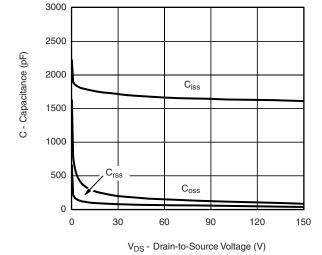


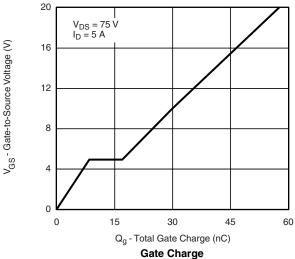


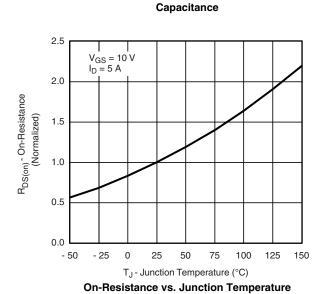


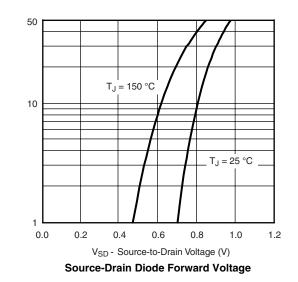
# TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

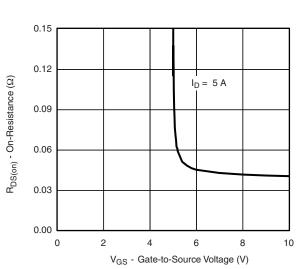












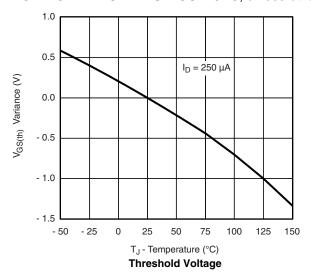
On-Resistance vs. Gate-to-Source Voltage

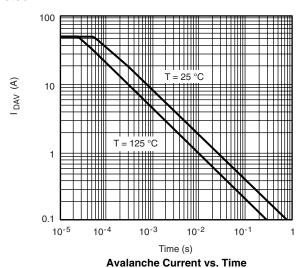
I<sub>S</sub> - Source Current (A)

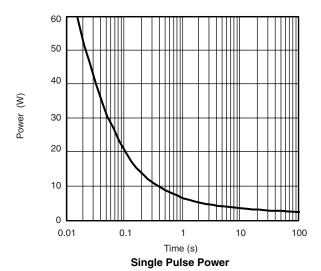
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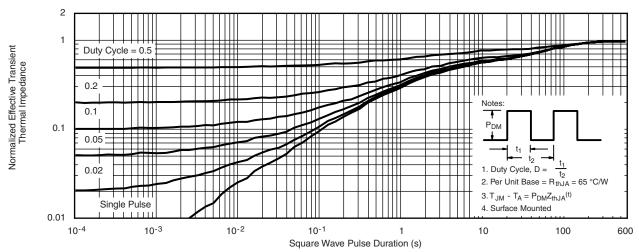
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# TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted





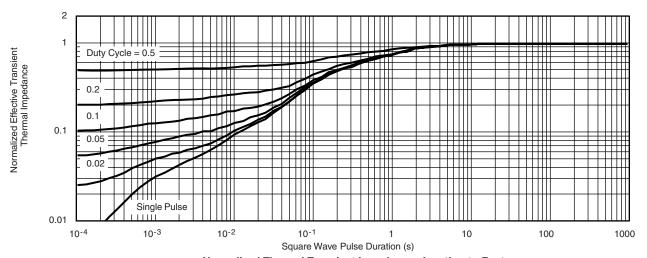




Normalized Thermal Transient Impedance, Junction-to-Ambient



# TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

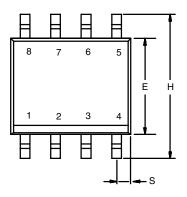


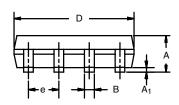
Normalized Thermal Transient Impedance, Junction-to-Foot

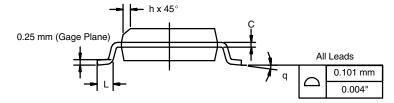
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SOIC (NARROW): 8-LEAD JEDEC Part Number: MS-012







	MILLIM	IETERS	INCHES			
DIM	Min	Max	Min	Max		
Α	1.35	1.75	0.053	0.069		
A <sub>1</sub>	0.10	0.20	0.004	0.008		
В	0.35	0.51	0.014	0.020		
С	0.19	0.25	0.0075	0.010		
D	4.80	5.00	0.189	0.196		
E	3.80	4.00	0.150	0.157		
е	1.27	BSC	0.050 BSC			
Н	5.80	6.20	0.228	0.244		
h	0.25	0.50	0.010	0.020		
L	0.50	0.93	0.020	0.037		
q	0°	8°	0°	8°		
S	0.44	0.64	0.018	0.026		
ECN: C-06527-Rev. I. 11-Sep-06						

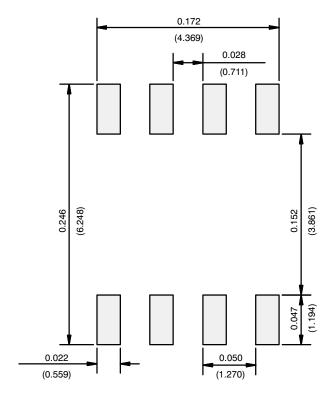
DWG: 5498

Document Number: 71192 www.vishay.com 11-Sep-06

# APPLICATION NOTE



# **RECOMMENDED MINIMUM PADS FOR SO-8**



Recommended Minimum Pads Dimensions in Inches/(mm)

Return to Index



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